

## isc N-Channel MOSFET Transistor

## AOI8N25

### FEATURES

- Drain Current –I\_D= 8.0A@ T\_C=25 $^\circ\!\mathrm{C}$
- Drain Source Voltage-: V<sub>DSS</sub>=250V(Min)
- Static Drain-Source On-Resistance : R<sub>DS(on)</sub> =0.56 Ω (Max)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### DESCRIPTION

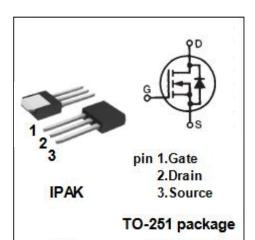
• Designed for use in switch mode power supplies and general purpose applications.

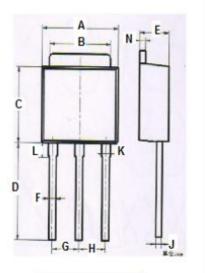
ADSOLU	ABSOLUTE WANTINOW RATINGS (Ta-25 C)					
SYMBOL	PARAMETER	VALUE				
V <sub>DSS</sub>	Drain-Source Voltage	250	V			
V <sub>GS</sub>	Gate-Source Voltage-Continuous	±30	V			
ID	Drain Current-Continuous	8.0	А			
I <sub>DM</sub>	Drain Current-Single Pluse	16	A			
PD	Total Dissipation @T <sub>c</sub> =25℃	78	W			
TJ	Max. Operating Junction Temperature	-50~150	°C			
T <sub>stg</sub>	Storage Temperature	-50~150	°C			

### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

# THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	1.6	°C/W





	mm	
DIM	MIN	MAX
Α	6.40	6.48
В	5.10	5.50
С	5.80	6.20
D	9.20	9.60
E	2.20	2.40
F	0.50	0.70
G	2.09	2.49
Н	2.09	2.49
J	0.40	0.60
Κ	0.70	0.90
L	1.60	2.00
N	0.40	0.60

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### **ELECTRICAL CHARACTERISTICS**

#### T<sub>c</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> = 0.25mA	250		V
V <sub>GS(th)</sub>	Gate Threshold Voltage V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> = 0.25mA		3.1	4.3	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> =1.5A		0.56	Ω
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±30V;V <sub>DS</sub> = 0		±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =250V; V <sub>GS</sub> = 0 V <sub>DS</sub> =200V; V <sub>GS</sub> = 0@T <sub>J</sub> =125℃		1 10	μA
V <sub>SD</sub>	Forward On-Voltage	I <sub>S</sub> = 1A; V <sub>GS</sub> = 0		1.0	V



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